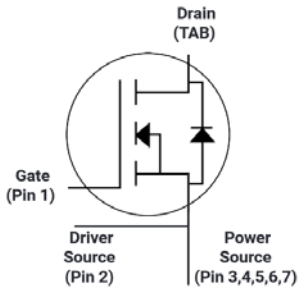
SCD212060B7GH

Silicon Carbide Power MOSFET （N-Channel Enhancement）

V_{DS}	1200V
$I_{D\ (25°C)}$	42A
$R_{DS(on)}$	60mΩ



Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free,

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- **Package**: TO263-7L
- **Terminals**: Tin plated leads
- **Polarity**: As marked

■Maximum Ratings (T_C=25℃ Unless otherwise specified）

PARAMTETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code			D212060B7GH		
Drain source voltage @ T_j=25°C	$V_{DS,max}$	V	1200	V_{GS}=0 V, I_D=100uA	
Gate source voltage @ T_j=25°C	$V_{GS,max}$	V	-10/+25	Absolute maximum values (AC f > 1Hz, duty cycle < 1%)	
Gate source voltage @ T_j=25°C	$V_{GS,op}$	V	-5/+20	Recommended operational values	
Continuous drain current @ T_c=25°C	I_D	A	42	V_{GS}=20V, Tc=25℃	Fig.14
Continuous drain current @ T_c=110°C			29	V_{GS}=20V, Tc=110℃	
Pulsed drain current	$I_{D(pulsed)}$	A	88.5	Pulse width tp limited by Tj,max	Fig.15
Avalanche energy, Single Pulse	E_{AS}	mJ	400	V_{DD}=75V, L=30mH	
Power Dissipation	P_{TOT}	W	234	T_c=25°C , Tj = 175℃	Fig.13
Operating junction and Storage temperature range	Tj ,Tstg	°C	-55 to +175		
Soldering temperature	T_L	°C	260	1.6mm (0.063'') from case for 10s	

■Static Electrical Characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	$V_{GS(th)}$	V	1.5	2.8	4.0	V_{DS}=10V, I_D= 20mA	Fig.4, 11
Drain source breakdown voltage	$V_{(BR)DSS}$	V	1200			V_{GS}=0V, I_D=100uA	
Zero gate voltage drain current	I_{DSS}	uA		<1	50	V_{DS}=1200V, V_{GS}= 0V	
				10	500	V_{DS}=1200V, V_{GS}= 0V, Tj= 175℃	
Gate source leakage current	I_{GSS}	nA			250	V_{GS}= 20V, V_{DS}=0V	
Current drain source on-state resistance	$R_{DS\ ON}$	mΩ		66	80	V_{GS}=20V, I_D=20A	Fig.3, 5, 6
				100		V_{GS}=20V, I_D=20A,Tj=175℃	
Transconductance	g_f	S		7.7		V_{DS}=20V,I_D=20A	

■Dynamic Electrical Characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	Ciss	pF		2200		V_{DS}=800V, V_{GS}=0V, Tj=25℃, f=1MHz, V_{AC}= 25mV	Fig.10
Output capacitance	Coss			115			
Reverse capacitance	Crss			18.5			
Coss stored energy	Eoss	uJ		47			Fig.12
Gate source charge	Qgs	nC		29		V_{DS}=800V, V_{GS}=-5/20V, I_D=20A	Fig.16
Gate drain charge	Qgd			64			
Gate charge	Qg			129			
Short-Circuit Withstand Time	t_{sc}	us		3.6		Rg=30Ω,ID=376A, VGS=-5/20V,VDD=800V	
Internal Gate Resistance	$R_{G(int)}$	Ω		2.0	5.0	f =1MHz, V_{AC}= 25mV	

■Switching Characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on delay time	$t_{d(on)}$	ns		5.9		V_{DD}=800V, V_{GS}=-5/+20V, I_D=20A, L=100uH, $R_{G(ext)}$= 2.7Ω	
Rise time	t_r			15			
Turn off delay time	$t_{d(off)}$			17.3			
Fall time	t_f			10			
Turn on switching energy	Eon	uJ		300			Fig.17, 18
Turn off switching energy	Eoff			45			

■Body diode characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	V_{SD}	V		4.0		V_{GS}=0V,I_{SD}=10A	Fig.8
Continuous diode forward current	I_S	A		43		V_{GS}=0V,Tc=25℃	
Reverse recovery time	trr	nS		57		V_{DS}=400V, V_{GS}=0V, I_{SD}=10A, di/dt=300A/uS	
Reverse recovery charge	Qrr	nC		109			
Peak reverse recovery current	Irrm	A		3.5			

■Thermal Characteristics （T_a=25℃ Unless otherwise specified）

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	$R_{\theta J-C}$	°C /W	0.64

■Typical Characteristics

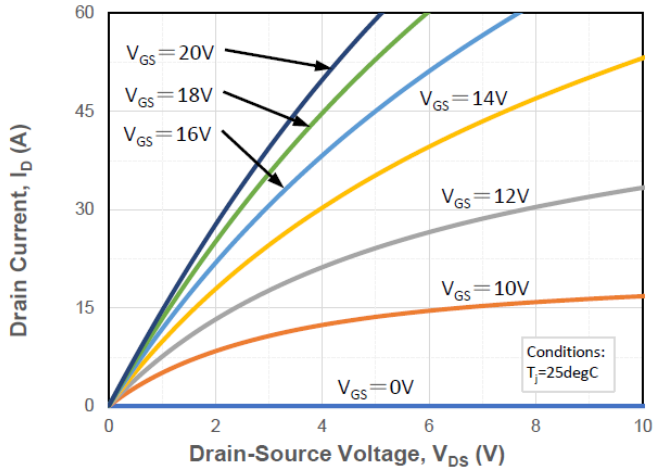


Figure 1. Output Characteristics Tj = 25℃

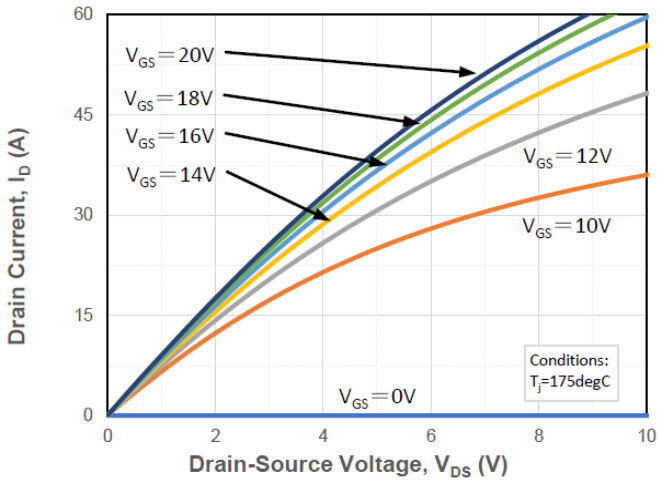


Figure 2. Output Characteristics Tj = 175℃

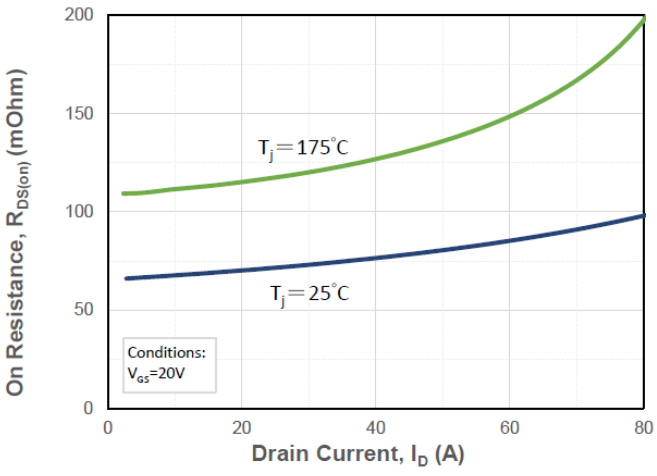


Figure 3. On-resistance vs. drain current

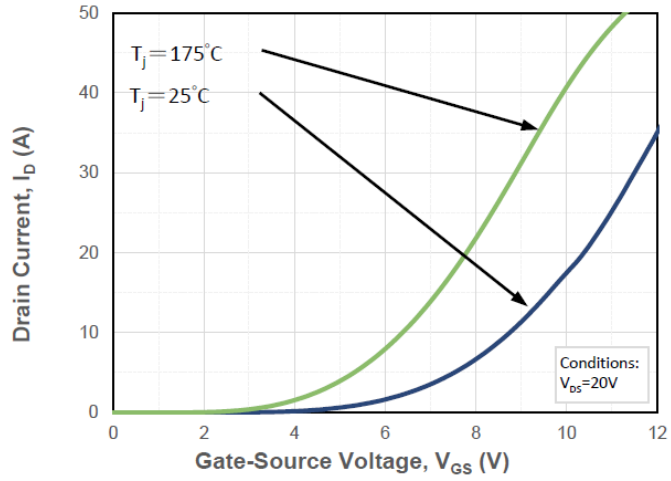


Figure 4. Transfer Characteristics for various Tj

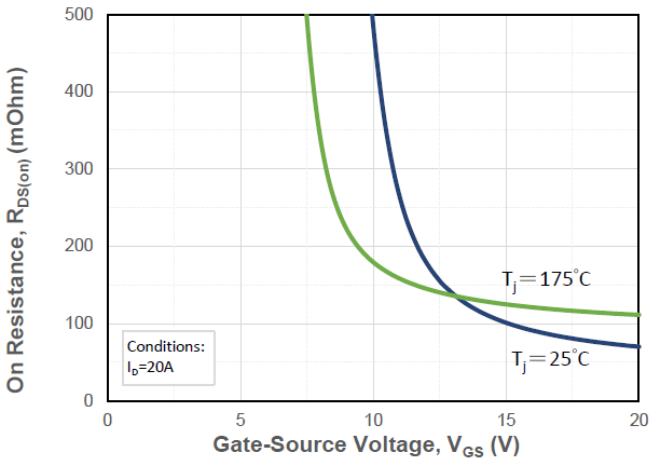


Figure 5. On-resistance vs. gate voltage for various Tj Gate voltage

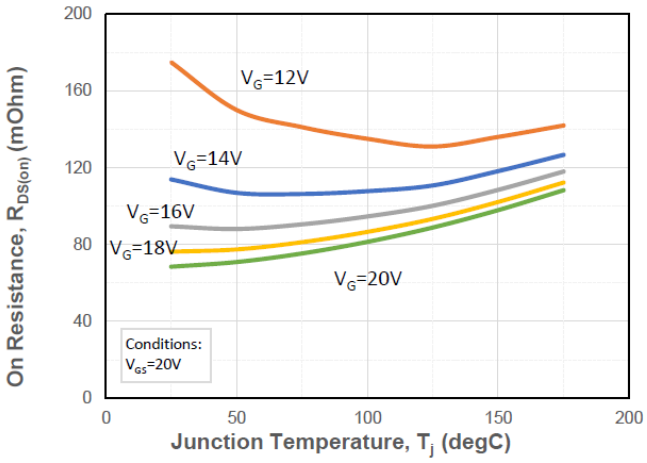


Figure 6. On-resistance vs. Temperature for various

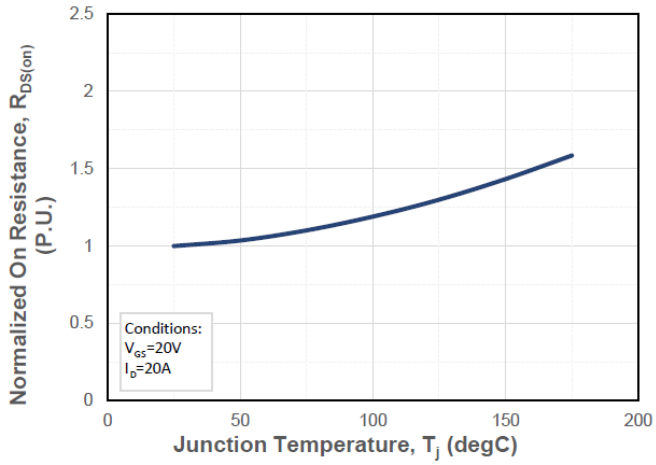


Figure 7. Normalized On-Resistance vs.Temperature

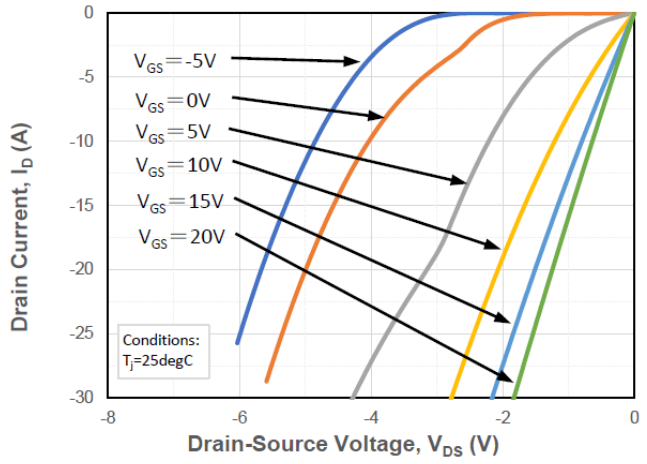


Figure 8. Reverse Output Characteristics at Tj = 25°C

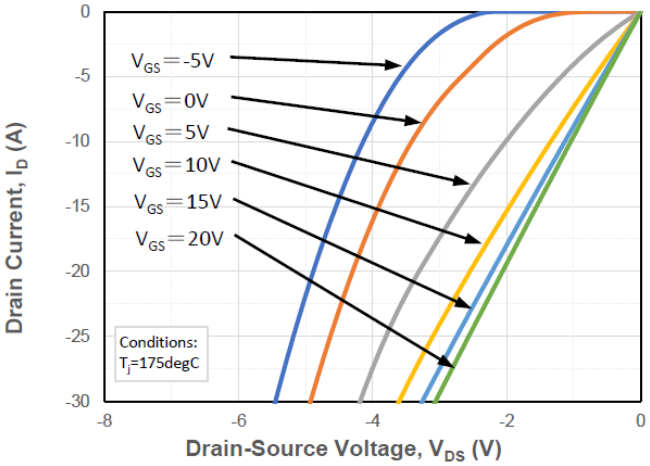


Figure 9. Reverse Output Characteristics at Tj = 175°C

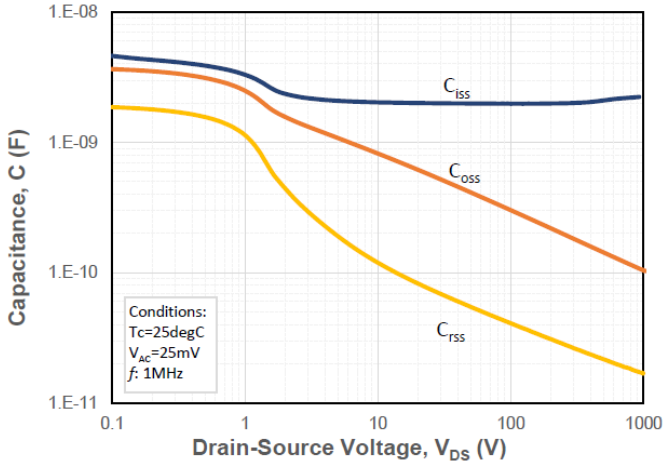


Figure 10. Capacitances vs. Drain to Source Voltage

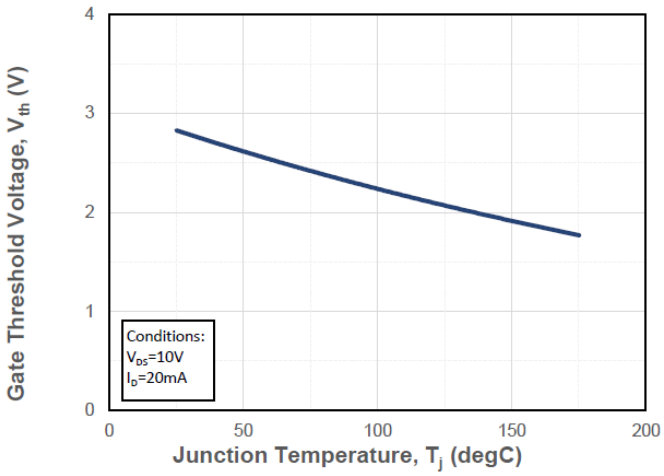


Figure 11. Threshold voltage vs.temperature

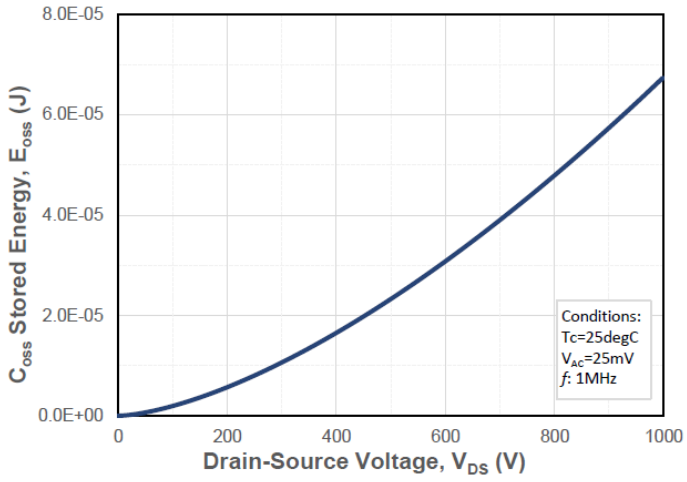


Figure 12. Output Capacitor Stored Energy

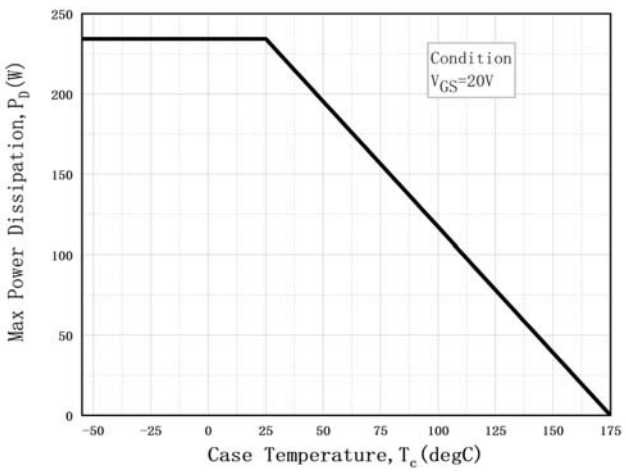


Figure 13. Maximum Power Dissipation Derating vs. Case Temperature

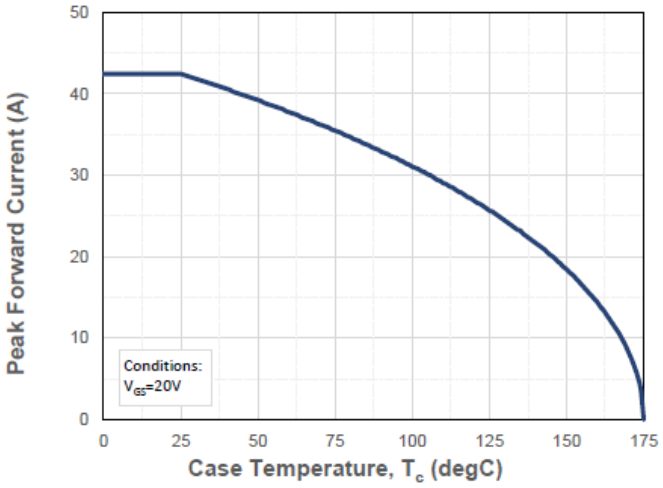


Figure 14. Drain Current Derating vs. Case Temperature

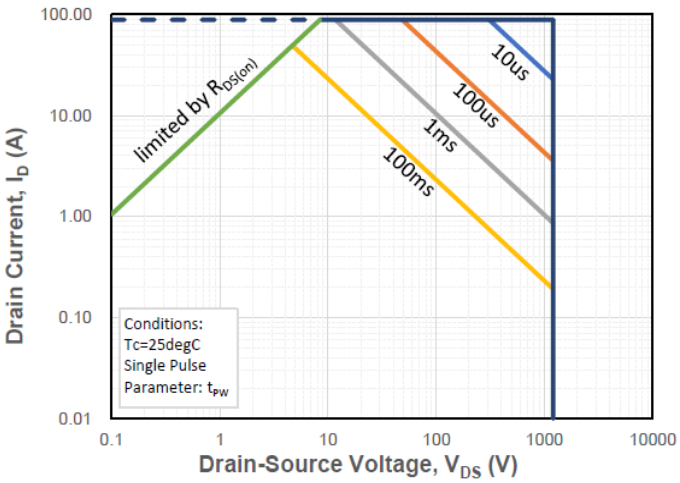


Figure 15. Safe Operating Area

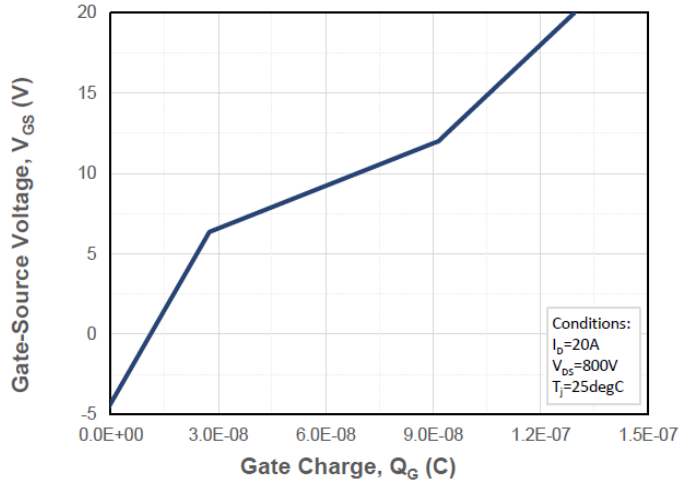


Figure 16. Gate Charge Characteristics

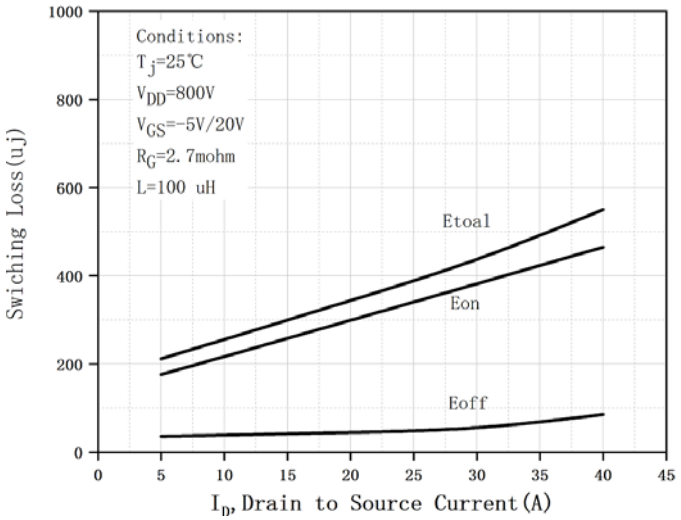


Figure 17. Clamped Inductive Switching Energy vs. Drain Current

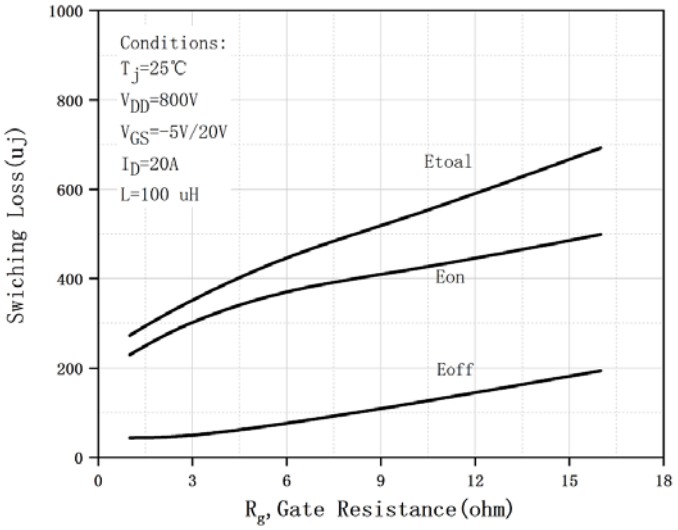


Figure 18. Clamped Inductive Switching Energy vs. External Gate Resistor (R_G(ext.))

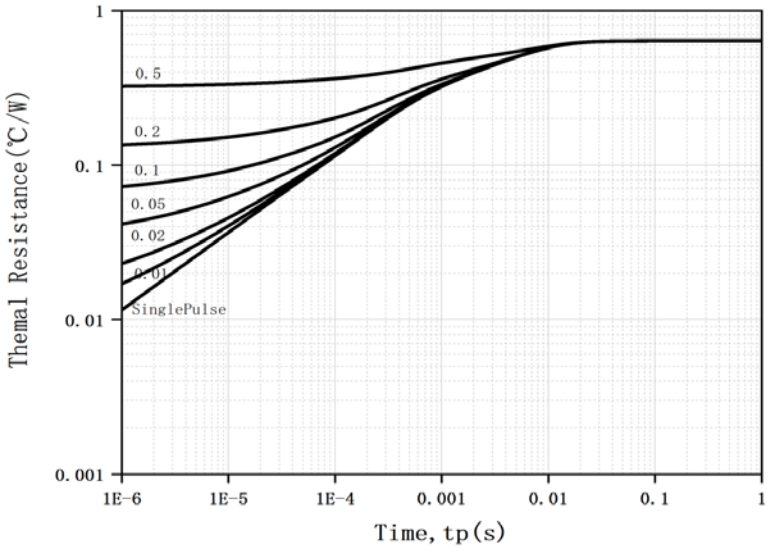


Figure 19. Transient Junction to Case Thermal Impedance

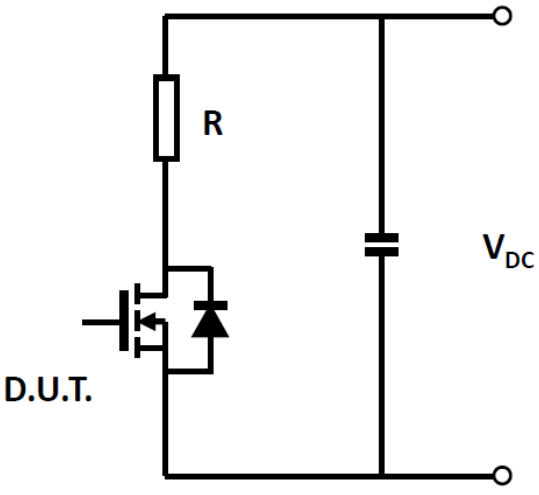


Figure 20. Schematic of Resistive Switching

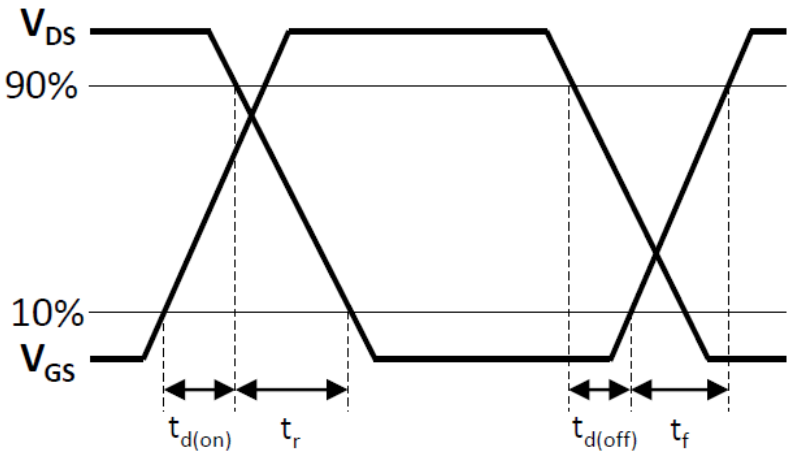
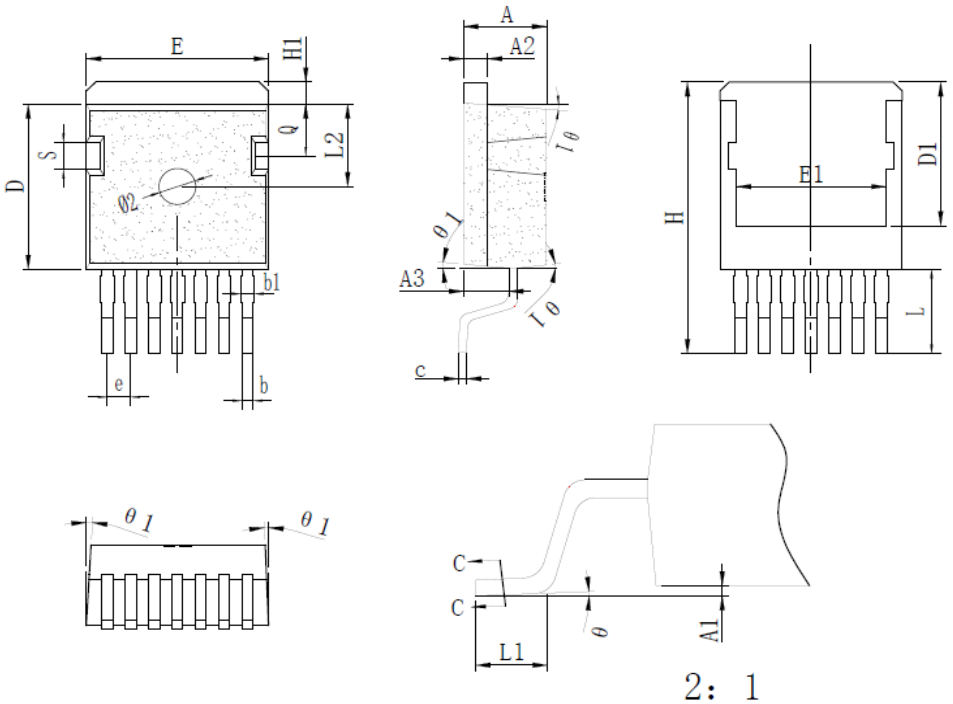
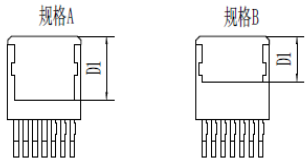


Figure 21. Switching Times Definition

■Outline Dimensions





✻为关键管控尺寸

SYMBOL	mm		
	MIN	NOM	MAX
✻A	4.30	4.40	4.50
✻A1	0.00	0.10	0.20
✻A2	1.22	1.27	1.32
✻A3	2.30	2.40	2.50
✻b	0.50	0.60	0.70
✻b1	-	-	0.63
✻c	0.45	0.50	0.55
✻D	9.15	9.30	9.45
D1	规格A：8.00REF 规格B：5.70REF		
✻E	10.12	10.16	10.20
E1	8.20	8.40	8.60
✻e	1.25	1.27	1.29
✻H	14.85	15.00	15.15
H1	1.10	1.20	1.30
✻L	4.50	4.70	4.90
L1	1.70	2.00	2.30
L2	4.55	4.65	4.75
S	1.40	1.50	1.60
Q	2.80	2.90	3.00
✻θ	0°	2.5°	8°
θ1	5°	7°	9°

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